

# SILICON POWER TRANSISTOR 2SD1481

# NPN SILICON EPITAXIAL TRANSISTOR (DARLINGTON CONNECTION) FOR LOW-FREQUENCY POWER AMPLIFIERS AND LOW-SPEED SWITCHING

#### **FEATURES**

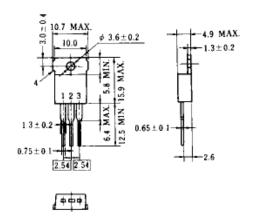
- On-chip C-to-B Zener diode for surge voltage absorption
- Low collector saturation voltage: Vce(SAT) = 1.5 V MAX. (at 1 A)
- Ideal for use in a direct drive from IC to the devices such as OA and FA equipment and motor solenoid relay printer head drivers

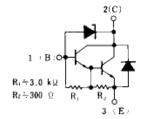
#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	60 ±10	V
Collector to emitter voltage	VCEO	60 ±10	٧
Emitter to base voltage	V <sub>EBO</sub>	7.0	٧
Collector current	Ic(DC)	2.0	Α
Collector current	IC(pulse)*	4.0	Α
Base current	I <sub>B(DC)</sub>	0.2	Α
Total power dissipation	P <sub>T</sub> (Tc = 25°C)	15	W
Total power dissipation	P⊤ (Ta = 25°C)	1.5	W
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

<sup>\*</sup> PW  $\leq$  300  $\mu$ s, duty cycle  $\leq$  10%

#### PACKAGE DRAWING (UNIT: mm)





Electrode Connection

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Fin (collector)

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# **ELECTRICAL CHARACTERISTICS (Ta = 25°C)**

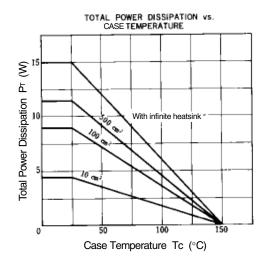
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = 40 V, I <sub>E</sub> = 0			1.0	μΑ
DC current gain	h <sub>FE1</sub>	$V_{CE} = 2.0 \text{ V}, I_{C} = 1.0 \text{ A}^*$	2,000		20,000	
DC current gain	h <sub>FE2</sub>	$V_{CE} = 2.0 \text{ V}, I_{C} = 3.0 \text{ A}^*$	500			
Collector saturation voltage	V <sub>CE(sat)</sub>	Ic = 1.0 A, I <sub>B</sub> = 1.0 mA*			1.5	V
Base saturation voltage	V <sub>BE(sat)</sub>	Ic = 1.0 A, I <sub>B</sub> = 1.0 mA*			2.0	V
Turn-on time	ton	$I_C = 1.0 \text{ A}, I_{B1} = -I_{B2} = 10 \text{ mA}$		0.5		μs
Storage time	<b>t</b> stg	R <sub>L</sub> = 50 Ω, V <sub>CC</sub> $\cong$ 50 V Refer to the test circuit.		2.0		μs
Fall time	<b>t</b> f	ricion to the test enount.		1.0		μs

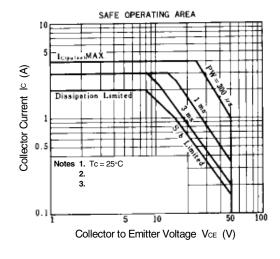
<sup>\*</sup> Pulse test PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2%

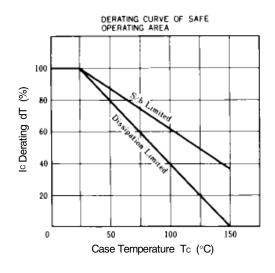
#### **hfe CLASSIFICATION**

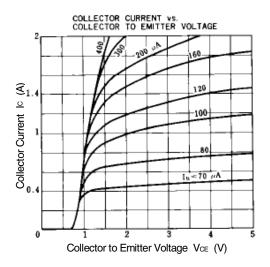
Marking	М	L	К
h <sub>FE1</sub>	2,000 to 5,000	4,000 to 10,000	8,000 to 20,000

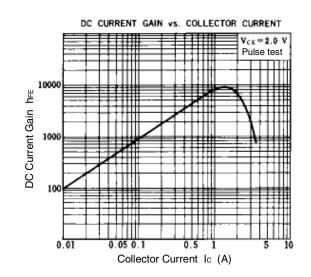
# TYPICAL CHARACTERISTICS (Ta = 25°C)

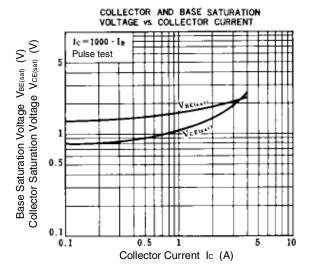




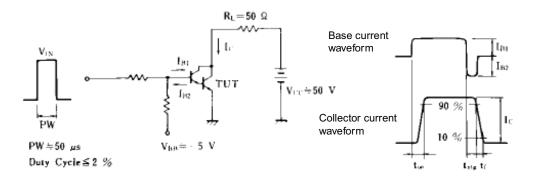








# SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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